



Features

- VDS = 20V
- RDS(ON) = 300mΩ (typ.) @ VGS= 2.5V
- RDS(ON) = 250mΩ (typ.) @ VGS= 4.5V
- ESD Protected up to 2KV

Application

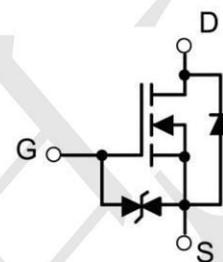
- Load/Power Switching
- Interfacing Switching
- Battery Management for Ultra Small Portable Electronics
- Logic Level Shift

Package and Pin Configuration



SOT523

Circuit diagram



Marking: A

Absolute Maximum Ratings ($T_A=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	20	V
Gate-Source Voltage	V_{GS}	± 8	V
Continuous Drain Current	I_D	0.9	A
Pulsed Drain Current ($t=300\mu\text{s}$) ⁽¹⁾	I_{DM}	1	A
Power Dissipation ⁽²⁾	P_D	0.27	W
Thermal Resistance from Junction to Ambient	$R_{\theta JA}$	833	°C/W
Junction Temperature	T_J	150	°C
Storage Temperature	T_{STG}	-55~+150	°C

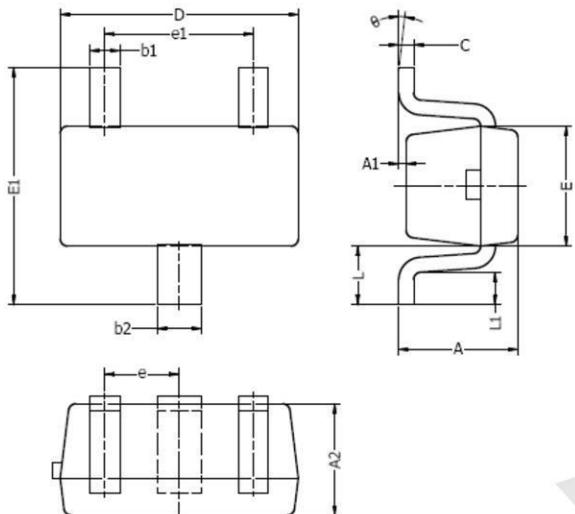


Electrical Characteristics ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Test Condition	Min	Type	Max	Unit
Static Characteristics						
Drain-source breakdown voltage	$V_{(\text{BR})\text{DSS}}$	$V_{\text{GS}} = 0\text{V}, I_D = 250\mu\text{A}$	20	25		V
Zero gate voltage drain current	I_{DSS}	$V_{\text{DS}} = 20\text{V}, V_{\text{GS}} = 0\text{V}$			1	μA
Gate-body leakage current	I_{GSS}	$V_{\text{GS}} = \pm 18\text{V}, V_{\text{DS}} = 0\text{V}$			± 10	μA
Gate threshold voltage ⁽³⁾	$V_{\text{GS}(\text{th})}$	$V_{\text{DS}} = V_{\text{GS}}, I_D = 250\mu\text{A}$	0.5	0.7	1.1	V
Drain-source on-resistance ⁽³⁾	$R_{\text{DS}(\text{on})}$	$V_{\text{GS}} = 4.5\text{V}, I_D = 500\text{mA}$		250	400	$\text{m}\Omega$
		$V_{\text{GS}} = 2.5\text{V}, I_D = 500\text{mA}$		300	500	
Forward transconductance	g_{FS}	$V_{\text{DS}} = 10\text{V}, I_D = 500\text{mA}$			1.2	S
Dynamic characteristics⁽⁴⁾						
Input Capacitance	C_{iss}	$V_{\text{DS}} = 10\text{V}, V_{\text{GS}} = 0\text{V}, f = 1\text{MHz}$		45		pF
Output Capacitance	C_{oss}			9		
Reverse Transfer Capacitance	C_{rss}			6		
Switching Characteristics⁽⁴⁾						
Turn-on delay time	$t_{\text{d}(\text{on})}$	$V_{\text{DD}} = 10\text{V}, I_D = 500\text{mA}, V_{\text{GS}} = 4.5\text{V}, R_G = 6\Omega$		20		ns
Turn-on rise time	t_r			90		
Turn-off delay time	$t_{\text{d}(\text{off})}$			750		
Turn-off fall time	t_f			400		
Source-Drain Diode characteristics						
Diode Forward voltage ⁽³⁾	V_{DS}	$I_S = 0.15\text{A}, V_{\text{GS}} = 0\text{V}$			1.3	V



SOT523 Package Outline Drawing



DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	0.70	0.90	0.028	0.035
A1	0.00	0.10	0.000	0.004
A2	0.70	0.80	0.028	0.031
b1	0.15	0.25	0.006	0.010
b2	0.25	0.35	0.010	0.014
c	0.10	0.20	0.004	0.008
D	1.50	1.70	0.059	0.067
E	0.70	0.90	0.028	0.035
E1	1.45	1.75	0.057	0.069
e	0.50 TYP.		0.020 TYP.	
e1	0.90	1.10	0.035	0.043
L	0.40 REF.		0.016 REF.	
L1	0.10	0.30	0.004	0.012
θ	0°	8°	0°	8°

NOTES:

1. Above package outline conforms to JEITA EAIJ ED-7500A SC-75A.
2. Dimensions are exclusive of Burrs, Mold Flash & Tie Bar extrusions.

